

UNR7231 (UN7231)

Silicon NPN epitaxial planar type

For low-frequency amplification

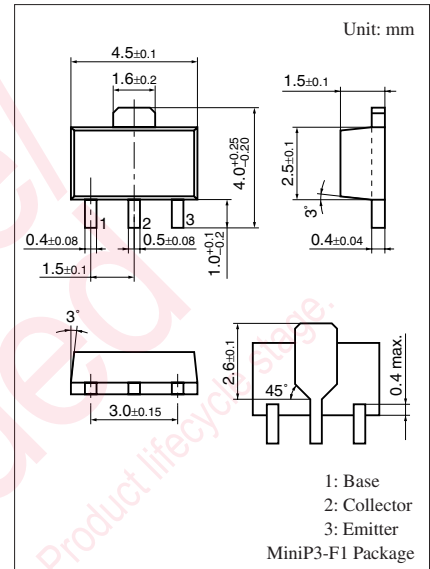
■ Features

- High forward current transfer ratio h_{FE}
- Costs can be reduced through downsizing of the equipment and reduction of the number of parts.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

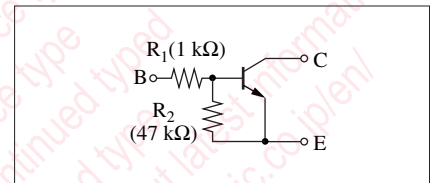
| Parameter | Symbol | Rating | Unit |
|---------------------------------------|-----------|-------------|------------------|
| Collector-base voltage (Emitter open) | V_{CBO} | 20 | V |
| Collector-emitter voltage (Base open) | V_{CEO} | 20 | V |
| Collector current | I_C | 0.7 | A |
| Peak collector current | I_{CP} | 1.5 | A |
| Total power dissipation * | P_T | 1.0 | W |
| Junction temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |

Note) *: Printed circuit board: Copper foil area of 1 cm² or more, and the board thickness of 1.7 mm for the collector portion



Marking Symbol: IC

Internal Connection

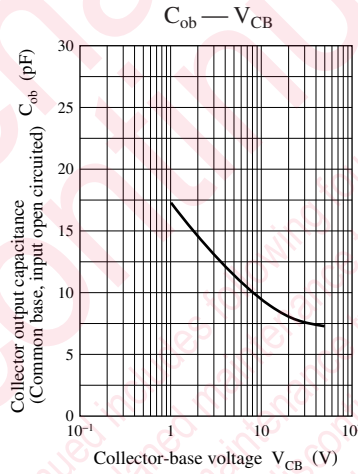
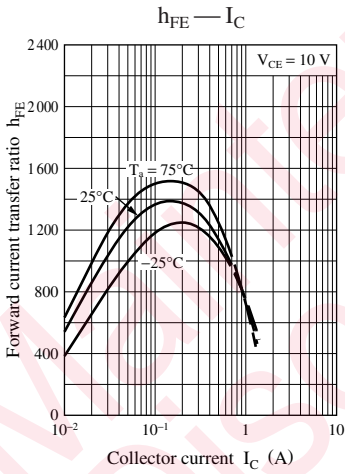
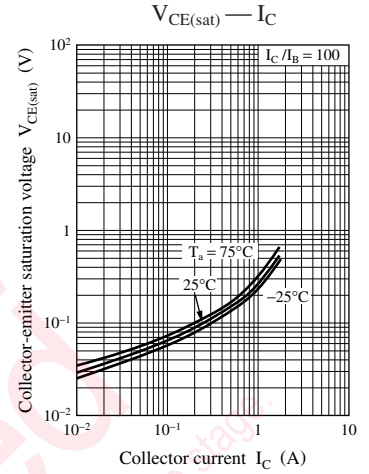
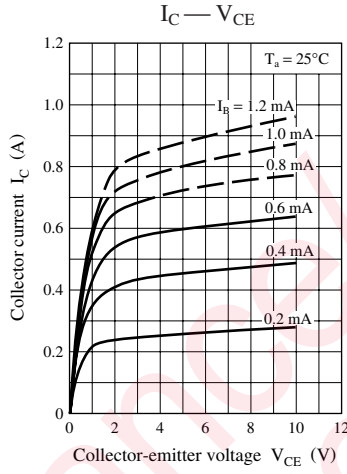
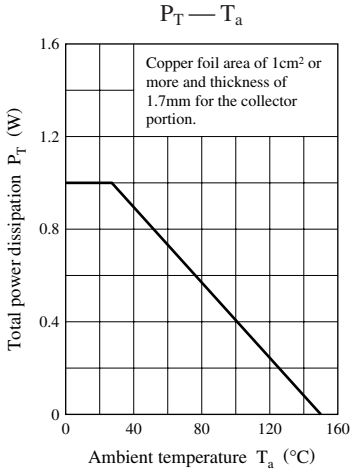


■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|--|---------------|--|-------|-------|-------|---------------|
| Collector-base voltage (Emitter open) | V_{CBO} | $I_C = 10 \mu\text{A}, I_E = 0$ | 20 | | | V |
| Collector-emitter voltage (Base open) | V_{CEO} | $I_C = 1 \text{ mA}, I_B = 0$ | 20 | | | V |
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{CB} = 15 \text{ V}, I_E = 0$ | | | 1 | μA |
| Collector-emitter cutoff current (Base open) | I_{CEO} | $V_{CE} = 15 \text{ V}, I_B = 0$ | | | 10 | μA |
| Emitter-base cutoff current (Collector open) | I_{EBO} | $V_{EB} = 14 \text{ V}, I_C = 0$ | | | 0.5 | mA |
| Forward current transfer ratio * | h_{FE} | $V_{CE} = 10 \text{ V}, I_C = 150 \text{ mA}$ | 800 | | 2 100 | — |
| Collector-emitter saturation voltage * | $V_{CE(sat)}$ | $I_C = 500 \text{ mA}, I_B = 5 \text{ mA}$ | | | 0.4 | V |
| Input resistance | R_1 | | 0.7 | 1.0 | 1.3 | k Ω |
| Resistance ratio | R_1/R_2 | | 0.016 | 0.021 | 0.025 | — |
| Transition frequency | f_T | $V_{CB} = 20 \text{ V}, I_E = -20 \text{ mA}, f = 200 \text{ MHz}$ | | 55 | | MHz |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.
2. *: Pulse measurement

Note) The part number in the parenthesis shows conventional part number.



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